

**REMARKS**

Claims 1 - 16 are pending in the present application, of which claim 1 has been canceled and claims 2 - 4, 7, 10, 12, 14 and 15 have been amended. Applicants respectfully submit that no new matter has been added. It is therefore believed that this Amendment is fully responsive to the Office Action dated **March 13, 2003**.

**IN THE DRAWINGS:**

Item 1 of the Office Action indicates that Figures 1 and 2 must be labeled as "Prior Art". A Request for Approval of Drawing Corrections is attached with corrected Figures 1 and 2. Applicants respectfully request approval of the corrections.

**Allowable Claim Subject Matter:**

Applicants gratefully acknowledge the indication in item 4 of the Office Action that claims 4 - 10 would be allowable, if amended, to include all of the limitations of the base claim and any intervening claims.

In view of the above, claims 4, 7 and 10 have been amended in independent form to include all of the limitations of the base claim and any intervening claims. Therefore, it is respectfully submitted that independent claims 4, 7 and 10 are allowable. Moreover, it is respectfully submitted



that claims 2, 4, 5, 6, 8, 9 and 11 - 16 are also allowable based on their respective dependency from allowable independent claims 3, 7 and 10.

Thus, it is respectfully asserted that all of the remaining pending claims 2 - 16 are indicated as being allowable over the prior art of record. Therefore, it is respectfully requested that the Examiner allow these claims, along with the entire application, to issue.

If, for any reason, it is felt that this application is not now in condition for allowance, the Examiner is requested to contact Applicants undersigned attorney at the telephone number indicated below to arrange for an interview to expedite the disposition of this case.

Attached hereto is a marked-up version of the changes made to the claims by the current amendment. The attached page is captioned "Version with markings to show changes made."

In the event that this paper is not timely filed, Applicants respectfully petition for an appropriate extension of time. Please charge any fees for such an extension of time and any other fees which may be due with respect to this paper, to Deposit Account No. 01-2340.

Respectfully submitted,

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PATENT TRADEMARK OFFICE

Enclosures: Version with markings to show changes made  
Request for Approval of Drawing Corrections

**VERSION WITH MARKINGS TO SHOW CHANGES MADE 10/090,612**

**IN THE CLAIMS**

Claims 2 - 4, 7, 10, 12, 14 and 15 have been **AMENDED** to read as follows:

2. (Amended) A high-frequency semiconductor device as set forth in claim ~~1~~ 4, wherein said antenna connection is an antenna line of a patterned conductor.

3. (Amended) A high-frequency semiconductor device as set forth in claim ~~1~~ 4, wherein said antenna connection is an active region formed in said semiconductor substrate.

4. (Amended) A high-frequency semiconductor device ~~as set forth in claim 1,~~ comprising:

an antenna-ground plane provided above a semiconductor substrate, to be connected to the ground potential;

a patch electrode provided on said antenna-ground plane with an interlayer insulation film therebetween;

an antenna connection provided under said antenna-ground plane and connected to said patch electrode via a through-hole formed passing through said antenna-ground plane; and

a line conductor provided above said semiconductor substrate, said line conductor forming a high-frequency transmission line together with the ground potential.

7. (Amended) A high-frequency semiconductor device ~~as set forth in claim 1~~, comprising:

an antenna-ground plane provided above a semiconductor substrate, to be connected to the ground potential;

a patch electrode provided on said antenna-ground plane with an interlayer insulation film therebetween;

an antenna connection provided under said antenna-ground plane and connected to said patch electrode via a through-hole formed passing through said antenna-ground plane; and

a line conductor provided on said antenna-ground plane with an interlayer insulation film therebetween, said line conductor forming a high-frequency transmission line together with said antenna-ground plane.

10. (Amended) A high-frequency semiconductor device ~~as set forth in claim 1~~, comprising:

an antenna-ground plane provided above a semiconductor substrate, to be connected to the ground potential;

a patch electrode provided on said antenna-ground plane with an interlayer insulation film therebetween and;

an antenna connection provided under said antenna-ground plane and connected to said patch electrode via a through-hole formed passing through said antenna-ground plane;

wherein a passive device is provided under said antenna-ground plane.



12. (Amended) A high-frequency semiconductor device as set forth in claim ~~1~~ 4, wherein said interlayer insulation film is composed of a resin insulating material.

14. (Amended) A high-frequency semiconductor device as set forth in claim ~~1~~ 4, wherein said patch electrode has a rectangular shape or a circular shape.

15. (Amended) A high-frequency semiconductor device as set forth in claim ~~1~~ 4, wherein each of said patch electrode and antenna-ground plane is ~~formed~~ formed of a high conductive material.